

L Number	Hits	Search Text	DB	Time stamp
-	59	(IR infrared (infra-red) (infra adj red) NIR MIR FIR SWIR MWIR LWIR) and ((mercury adj cadmium adj telluride) HgCdTe MCT) and (((readout (read adj out) read-out) adj (integrated-circuit (integrated adj circuit) IC)) ROIC)	USPAT; US-PGPUB; IBM_TDB	2003/05/08 12:02
-	38	((mercury adj cadmium adj telluride) HgCdTe MCT) and ((silicon si) adj substrate) and (lattice adj mismatch)	USPAT; US-PGPUB; IBM_TDB	2003/05/08 13:12
-	64	((mercury adj cadmium adj telluride) HgCdTe MCT) and (((readout (read adj out) read-out) adj (integrated-circuit (integrated adj circuit) IC)) ROIC)	USPAT; US-PGPUB; IBM_TDB	2003/05/08 13:21
-	33	(mesa with slope) same angle	USPAT; US-PGPUB; IBM_TDB	2003/05/08 13:26
-	94	(hydrofluoric adj acid) and (ammonium adj fluoride) and ((si silicon) adj surface) and (terminated bonded bonding dihydride)	USPAT; US-PGPUB; IBM_TDB	2003/05/08 13:34
-	16	((mercury adj cadmium adj telluride) HgCdTe MCT) and (hydrofluoric adj acid) and (passivate passivated passivating passivation)	USPAT; US-PGPUB; IBM_TDB	2003/05/08 13:51
-	18	(etch etcher etchant etching) with (bromine with (hydrobromic adj acid))	USPAT; US-PGPUB; IBM_TDB	2003/05/08 13:53
-	20	(ammonium adj fluoride) with (((si silicon) adj surface) (passivate passivated passivating passivation))	USPAT; US-PGPUB; IBM_TDB	2003/05/08 13:54
-	8	(dihydride) with ((si silicon) adj surface)	USPAT; US-PGPUB; IBM_TDB	2003/05/08 13:57
-	48	(clean cleaning) with ((si silicon) adj surface) with (hydrofluoric adj acid)	USPAT; US-PGPUB; IBM_TDB	2003/05/08 13:57